



A Product Line of Diodes Incorporated



#### 350V PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR IN SOT23

#### **Features and Benefits**

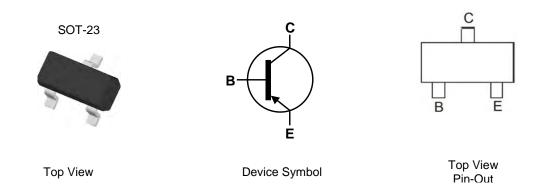
- BV<sub>CEO</sub> > -350V
- Maximum Continuous Collector Current I<sub>C</sub> = -500mA
- 330mW power dissipation
- Complementary part number FMMT6517
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT-23
- UL Flammability Rating 94V-0
- Case material: molded Plastic.
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

#### Applications

Power switches



## Ordering Information (Note 3)

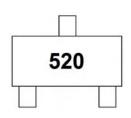
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT6520TA	520	7	8	3,000

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com

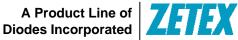
3. For Packaging Details, go to our website at http://www.diodes.com.

## **Marking Information**



520 = Product Type Marking Code





**FMMT6520** 

#### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-350	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-350	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Continuous Collector Current	Ιc	-500	mA

### Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 4)	P <sub>D</sub>	330	mW
Thermal Resistance, Junction to Ambient	(Note 4)	R <sub>0JA</sub>	379	°C/W
Thermal Resistance, Junction to Lead	(Note 5)	R <sub>θJL</sub>	350	°C/W
Operating and Storage Temperature Range		T <sub>J.</sub> T <sub>STG</sub>	-55 to +150	°C

4. For a device surface mounted FR4 PCB with minimum recommended pad layout; high coverage of single sided 1 oz copper, in still air conditions; the Notes: device is measured when operating in a steady-state condition. 5. Thermal resistance from junction to solder-point (at the end of the collector lead).

# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-350			V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 6)	BV <sub>CEO</sub>	-350			V	$I_{\rm C} = -1  \text{mA}$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5			V	I <sub>E</sub> = -10μA
Collector Cutoff Current	I <sub>СВО</sub>			-50	nA	V <sub>CB</sub> = -250V
Emitter Cutoff Current	I <sub>EBO</sub>			-50	nA	$V_{EB} = -3V$
Static Forward Current Transfer Ratio (Note 6)	h <sub>FE</sub>	20 30 30 20 15		200 200		$ \begin{array}{l} I_{\rm C} = -1 m A, \ V_{\rm CE} = -10 V \\ I_{\rm C} = -10 m A, \ V_{\rm CE} = -10 V \\ I_{\rm C} = -30 m A, \ V_{\rm CE} = -10 V \\ I_{\rm C} = -50 m A, \ V_{\rm CE} = -10 V \\ I_{\rm C} = -100 m A, \ V_{\rm CE} = -10 V \end{array} $
Collector-Emitter Saturation Voltage (Note 6)	V <sub>CE(sat)</sub>			-300 -350 -500 -1000	mV mV mV mV	$\begin{array}{l} I_{\rm C} = - \ 10mA, \ I_{\rm B} = -1mA \\ I_{\rm C} = - \ 20mA, \ I_{\rm B} = -2mA \\ I_{\rm C} = -30mA, \ I_{\rm B} = -3mA \\ I_{\rm C} = -50mA, \ I_{\rm B} = -5mA \end{array}$
Base-Emitter Saturation Voltage(Note 6)	V <sub>BE(sat)</sub>			-750 -850 -900	mV	$I_{C} = -10mA, I_{B} = -1mA$ $I_{C} = -20mA, I_{B} = -2mA$ $I_{C} = -30mA, I_{B} = -3mA$
Base-Emitter Turn-On Voltage(Note 6)	V <sub>BE(on)</sub>			-2.0	V	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -10V
Output Capacitance	C <sub>obo</sub>			6	pF	$V_{CB} = -20V, f = 1MHz$
Transition Frequency	f <sub>T</sub>	50			MHz	$V_{CE} = -20V$ , $I_C = -10mA$ , f = 20MHz

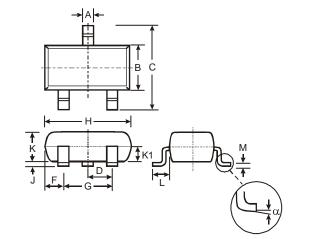
6. Measured under pulsed conditions. Pulse width ≤ 300  $\mu$ s. Duty cycle ≤ 2% Note:





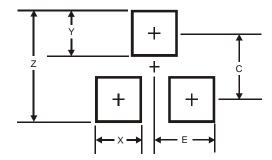


# **Package Outline Dimensions**



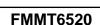
SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
Κ	0.903	1.10	1.00		
<b>K</b> 1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35





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